

HAT2197R

Silicon N Channel Power MOS FET Power Switching

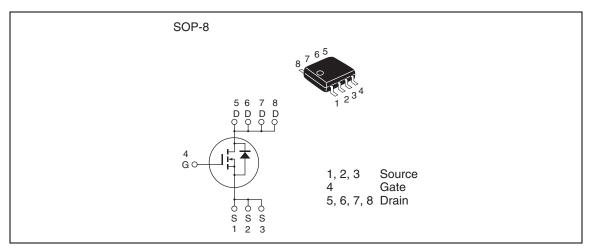
REJ03G0061-0201Z Rev.2.01 Nov.30.2016

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)}$ = 5.3 m Ω typ. (at V_{GS} = 10 V)

Outline





Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	16	А
Drain peak current	Note1 I _{D(pulse)}	128	А
Body-drain diode reverse drain current	I _{DR}	16	А
Avalanche current	I _{AP} Note 2	16	А
Avalanche energy	EAR Note 2	25.6	mJ
Channel dissipation	Pch Note3	2.5	W
Channel to ambient thermal impedance	θch-a ^{Note3}	50	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

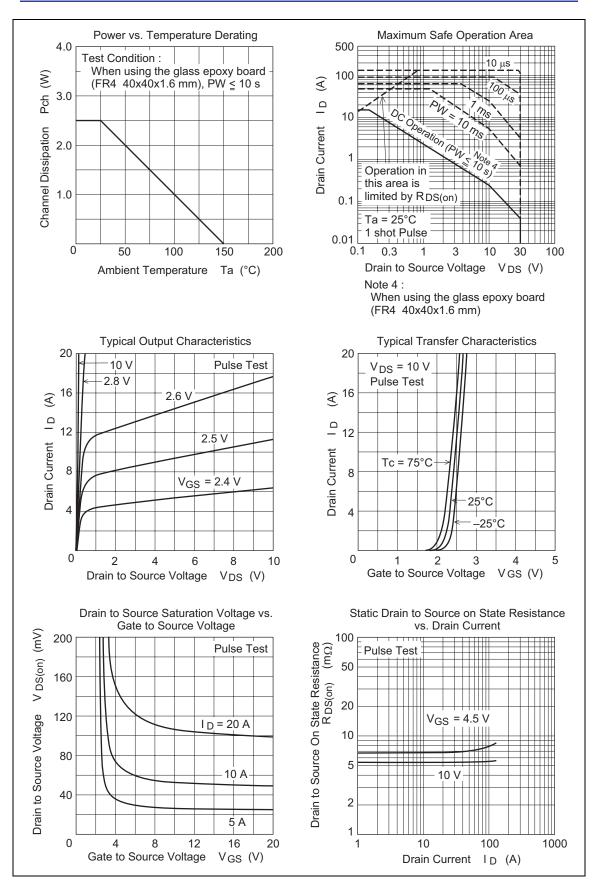
2. Value at Tch = 25°C, Rg \geq 50 Ω

3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10s

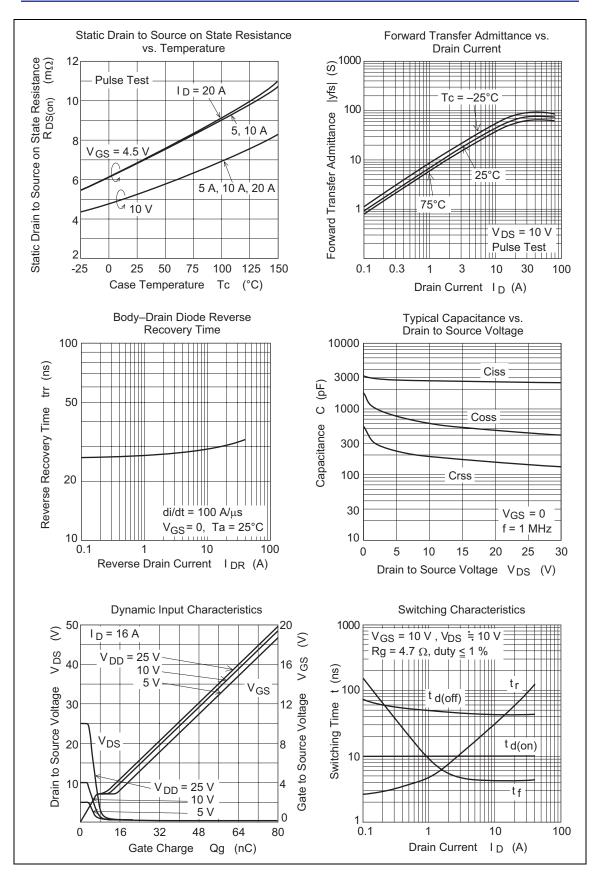
Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_		V	I_{D} = 10 mA, V_{GS} = 0
Gate to source leak current	I _{GSS}	—	—	± 0.1	μA	V_{GS} = ±20 V, V_{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	_	1	μA	V_{DS} = 30 V, V_{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	1.0	_	2.5	V	V_{DS} = 10 V, I _D = 1 mA
Static drain to source on state	R _{DS(on)}	_	5.3	6.7	mΩ	I_D = 8 A, V_{GS} = 10 V ^{Note4}
resistance	R _{DS(on)}	—	6.8	9.9	mΩ	I_D = 8 A, V_{GS} = 4.5 V ^{Note4}
Forward transfer admittance	y _{fs}	22	38	_	S	$I_D = 8 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2650		pF	V _{DS} = 10 V
Output capacitance	Coss	_	610		pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	190		pF	f = 1 MHz
Gate Resistance	Rg	_	1.2	_	Ω	
Total gate charge	Qg	_	18	_	nC	V _{DD} = 10 V
Gate to source charge	Qgs	_	7.5	_	nC	V _{GS} = 4.5 V
Gate to drain charge	Qgd	_	4.2		nC	I _D = 16 A
Turn-on delay time	t _{d(on)}	_	10	_	ns	V _{GS} = 10 V, I _D = 8 A
Rise time	tr	_	25	_	ns	 V _{DD} ≅ 10 V
Turn-off delay time	t _{d(off)}	_	45	_	ns	R _L = 1.25 Ω
Fall time	t _f	_	4.2		ns	Rg = 4.7 Ω
Body-drain diode forward voltage	V _{DF}	_	0.80	1.04	V	$IF = 16 A, V_{GS} = 0^{Note4}$
Body–drain diode reverse recovery time	t _{rr}	_	30	—	ns	IF = 16 A, V _{GS} = 0 diF/ dt = 100 A/ μs
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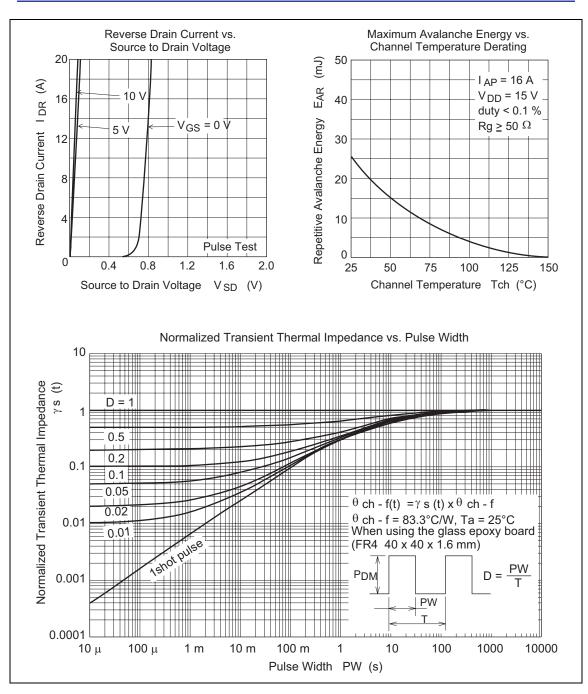
Notes: 4. Pulse test



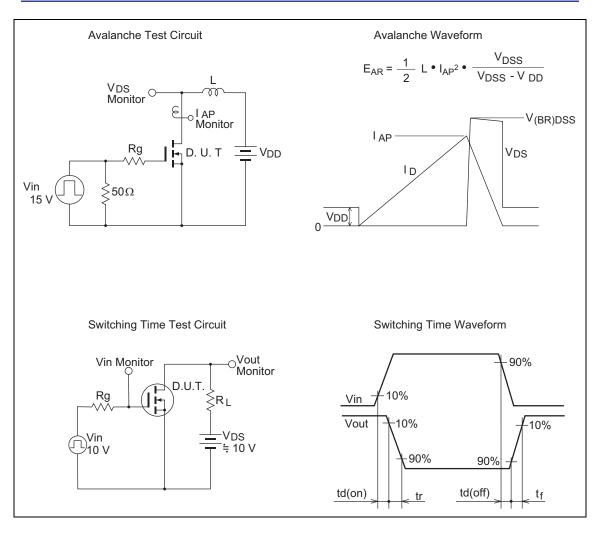
RENESAS



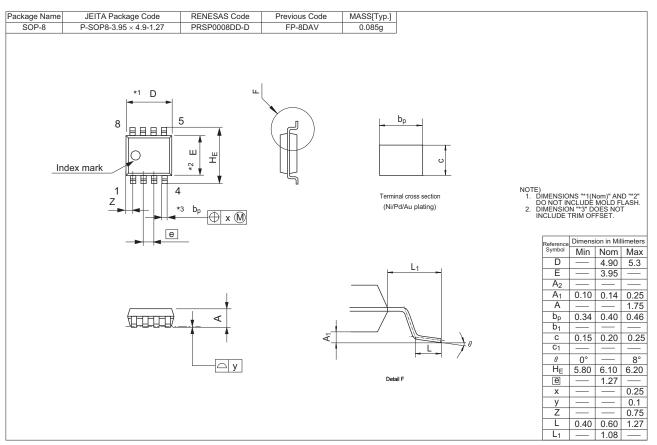
RENESAS



HAT2197R



Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
HAT2197R-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

General Precautions in the Handling of Power MOSFET and IGBT Products

The following usage notes are applicable to general purpose Power MOSFET and IGBT products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Derating

Continuous heavy condition (e.g. high temperature/voltage/current or high variation of temperature) may affect a reliability even if it are within the absolute maximum ratings. Please consider derating condition for appropriate reliability in reference Renesas Semiconductor Reliability Handbook (Recommendation for Handling and Usage of Semiconductor Devices) and individual reliability data.

2. Quality grade

- The quality grade of this product is "Standard".
- If you plan to use this product to "High quality" application, please inform to Renesas.
- Fail safe system is necessary to prevent malfunction even if this product is broken.

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